HARRIS SEMICONDUCTOR

CD74HC251, CD74HCT251

High Speed CMOS Logic 8-Input Multiplexer; Three-State

November 1997

Features

- Selects One of Eight Binary Data Inputs
- Three-State Output Capability
- True and Complement Outputs
- Typical (Data to Output) Propagation Delay of 14ns at V_{CC} = 5V, C_L = 15pF, T_A = 25°C
- Fanout (Over Temperature Range)
  - Standard Outputs . . . . . 10 LSTTL Loads
  - Bus Driver Outputs . . . . . 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips
  - HC Types
  - 2V to 6V Operation
  - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
  - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}

Description

The Harris CD74HC251 and CD74HCT251 are 8-channel digital multiplexers with three-state outputs, fabricated with high-speed silicon-gate CMOS technology. Together with the low power consumption of standard CMOS integrated circuits, they possess the ability to drive 10 LSTTL loads. The three-state feature makes them ideally suited for interfacing with bus lines in a bus-oriented system.

This multiplexer features both true (Y) and complement ($\overline{Y}$) outputs as well as an output enable ($\overline{OE}$) input. The $\overline{OE}$ must be at a low logic level to enable this device. When the $\overline{OE}$ input is high, both outputs are in the high-impedance state. When enabled, address information on the data select inputs determines which data input is routed to the Y and $\overline{Y}$ outputs. The CD74HCT251 logic family is speed, function, and pin-compatible with the standard 74LS251.

Ordering Information

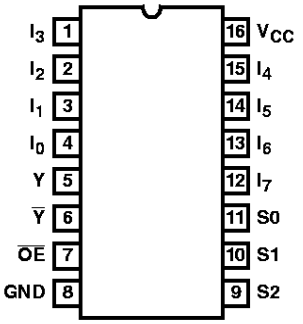
PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC251E	-55 to 125	16 Ld PDIP	E16.3
CD74HCT251E	-55 to 125	16 Ld PDIP	E16.3
CD74HC251M	-55 to 125	16 Ld SOIC	M16.15
CD74HCT251M	-55 to 125	16 Ld SOIC	M16.15

NOTES:

1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer or die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Pinout

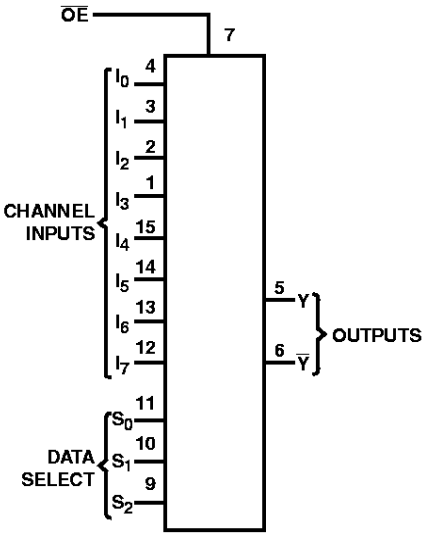
CD74HC251, CD74HCT251
(PDIP, SOIC)
TOP VIEW



CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

File Number **1489.1**

Functional Diagram



TRUTH TABLE

INPUTS				OUTPUT	
SELECT			OUTPUT CONTROL $\overline{OE}$	Y	$\overline{Y}$
S2	S1	S0			
X	X	X	H	Z	Z
L	L	L	L	I_0	$\overline{I}_0$
L	L	H	L	I_1	$\overline{I}_1$
L	H	L	L	I_2	$\overline{I}_2$
L	H	H	L	I_3	$\overline{I}_3$
H	L	L	L	I_4	$\overline{I}_4$
H	L	H	L	I_5	$\overline{I}_5$
H	H	L	L	I_6	$\overline{I}_6$
H	H	H	L	I_7	$\overline{I}_7$

NOTE: H = High Voltage Level, L = Low Voltage Level, X = Don't Care, Z = High Impedance (Off), I_0, I_1...I_7 = the level of the respective input.

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Drain Current, per Output, I_O
For -0.5V < V_O < V_{CC} +0.5V . . . . . ±25mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} . . . . . ±50mA

Operating Conditions

Temperature Range (T_A) . . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 3) θ_{JA} (°C/W)
PDIP Package 90
SOIC Package 160
Maximum Junction Temperature . . . . . 150°C
Maximum Storage Temperature Range . . . . . -65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . . 300°C
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA
Three-State Leakage Current	-	V_{IL} or V_{IH}	V_O = V_{CC} or GND	6	-	-	±0.5	-	±5.0	-	±10	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	0	5.5	-		±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Three-State Leakage Current	-	V_{IL} or V_{IH}	V_O = V_{CC} or GND	6	-	-	±0.5	-	±5.0	-	±10	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC}	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE: For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
S0, S1, S2	0.55
I0 - I7	0.5
$\overline{OE}$	2.65

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Table, e.g., 360µA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay Select to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	245	-	305	-	370	ns
			4.5	-	-	49	-	61	-	74	ns
		C_L =15pF	5	-	21	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	42	-	52	-	63	ns
Data to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	175	-	220	-	265	ns
			4.5	-	-	35	-	44	-	53	ns
		C_L =15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	30	-	37	-	45	ns
Enable to High Z and Enable from High Z	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	140	-	175	-	210	ns
			4.5	-	-	28	-	35	-	42	ns
		C_L =15pF	5	-	11	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	24	-	30	-	36	ns
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	2	-	-	75	-	95	-	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	C_{IN}	-	-	-	-	10	-	10	-	10	pF
Three-State Output Capacitance	CO	-	-	-	-	15	-	15	-	15	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	-	5	-	60	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay Select to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	42	-	53	-	63	ns
		C_L =15pF	5	-	18	-	-		-	-	ns
Data to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	35	-	44	-	53	ns
		C_L =15pF	5	-	12	-	-	-	-	-	ns
Enable to High Z and Enable from High Z	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-		30	-	38	-	45	ns
		C_L =15pF	5	-	12	-	-	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	C_{IN}	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	-	5		60	-	-	-	-	-	pF

NOTES:

4. C_{PD} is used to determine the dynamic power consumption, per package.
5. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = input frequency, C_L = output load capacitance, V_{CC} = supply voltage.

Test Circuits and Waveforms

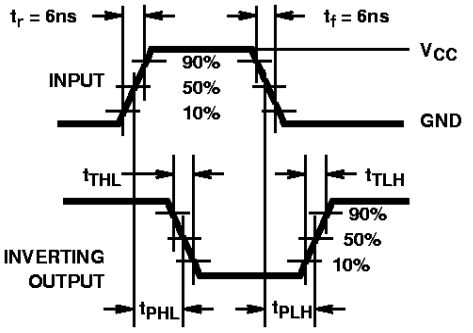


FIGURE 1. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

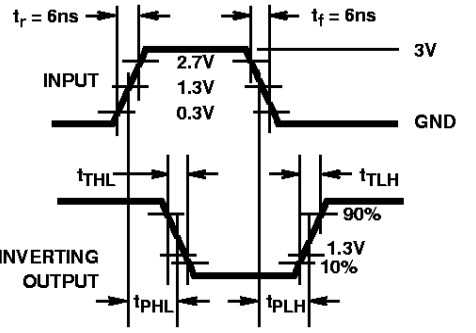


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

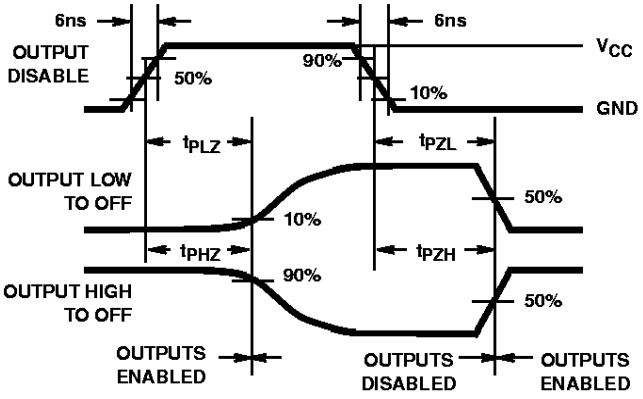


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

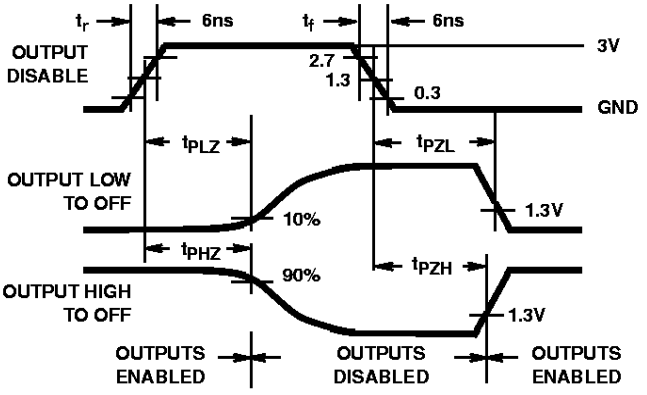
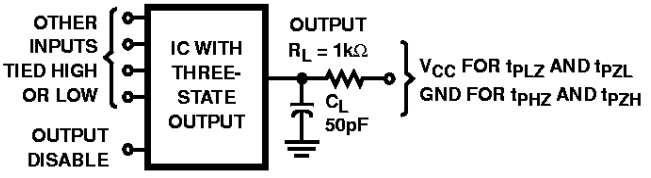


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output R_L = 1kΩ to V_{CC}, C_L = 50pF.

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT